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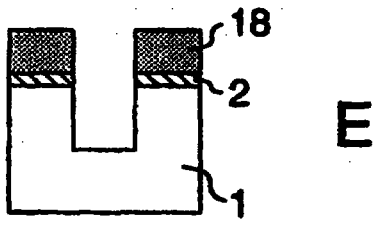
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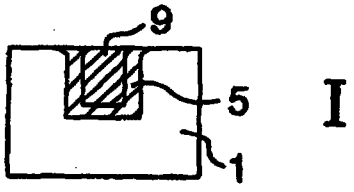
(54) Title: SEMICONDUCTOR DEVICE AND METHOD OF FABRICATING THE SAME

(57) Abstract

In a semiconductor device having a trench isolation structure, after a trench surface is selectively oxidized by a conventional method, an oxidation prevention film is removed, the entire surface of the substrate is again oxidized while only an oxide film on the substrate or trench surface is exposed, and a radius of curvature is provided to the shape of the oxide film near the trench upper end portion.



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